



ON Semiconductor®

FCA20N60

N-Channel SuperFET® MOSFET

600 V, 20 A, 190 mΩ

Features

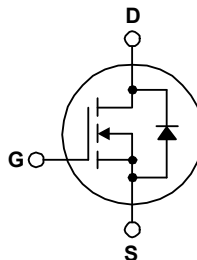
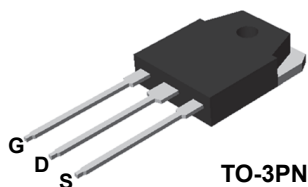
- 650V @ $T_J = 150^\circ\text{C}$
- Typ. $R_{DS(on)} = 150\text{ m}\Omega$
- Ultra Low Gate Charge (Typ. $Q_g = 75\text{ nC}$)
- Low Effective Output Capacitance (Typ. $C_{oss(eff.)} = 165\text{ pF}$)
- 100% Avalanche Tested

Applications

- Solar Inverter
- AC-DC Power Supply

Description

SuperFET® MOSFET is ON Semiconductor's first generation of high voltage super-junction (SJ) MOSFET family that is utilizing charge balance technology for outstanding low on-resistance and lower gate charge performance. This technology is tailored to minimize conduction loss, provide superior switching performance, dv/dt rate and higher avalanche energy. Consequently, SuperFET MOSFET is very suitable for the switching power applications such as PFC, server/telecom power, FPD TV power, ATX power and industrial power applications.



MOSFET Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter		FCA20N60 / FCA20N60-F109	Unit
V _{DSS}	Drain to Source Voltage		600	V
V _{GSS}	Gate-Source voltage		±30	V
I _D	Drain Current	- Continuous (T _C = 25°C)	20	A
		- Continuous (T _C = 100°C)	12.5	
I _{DM}	Drain Current	- Pulsed (Note 1)	60	A
E _{AS}	Single Pulsed Avalanche Energy (Note 2)		690	mJ
I _{AR}	Avalanche Current (Note 1)		20	A
E _{AR}	Repetitive Avalanche Energy (Note 1)		20.8	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)		4.5	V/ns
P _D	Power Dissipation	(T _C = 25°C)	208	W
		- Derate Above 25°C	1.67	W/°C
T _J , T _{STG}	Operating and Storage Temperature Range		-55 to +150	°C
T _L	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds		300	°C

Thermal Characteristics

Symbol	Parameter	FCA20N60 / FCA20N60_F109	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	0.6	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max.	41.7	

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FCA20N60	FCA20N60	TO-3PN	Tube	N/A	N/A	30 units
FCA20N60-F109	FCA20N60	TO-3PN	Tube	N/A	N/A	30 units

Electrical Characteristics $T_C = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
--------	-----------	-----------------	------	------	------	------

Off Characteristics

BV_{DSS}	Drain to Source Breakdown Voltage	$I_D = 250\ \mu\text{A}$, $V_{GS} = 0\ \text{V}$, $T_J = 25^\circ\text{C}$	600	-	-	V
		$I_D = 250\ \mu\text{A}$, $V_{GS} = 0\ \text{V}$, $T_J = 150^\circ\text{C}$	-	650	-	V
$\Delta BV_{DSS} / \Delta T_J$	Breakdown Voltage Temperature Coefficient	$I_D = 250\ \mu\text{A}$, Referenced to 25°C	-	0.6	-	V/ $^\circ\text{C}$
BV_{DS}	Drain-Source Avalanche Breakdown Voltage	$V_{GS} = 0\ \text{V}$, $I_D = 20\ \text{A}$	-	700	-	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 600\ \text{V}$, $V_{GS} = 0\ \text{V}$	-	-	1	μA
		$V_{DS} = 480\ \text{V}$, $T_C = 125^\circ\text{C}$	-	-	10	
I_{GSS}	Gate to Body Leakage Current	$V_{GS} = \pm 30\ \text{V}$, $V_{DS} = 0\ \text{V}$	-	-	± 100	nA

On Characteristics

$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}$, $I_D = 250\ \mu\text{A}$	3.0	-	5.0	V
$R_{DS(on)}$	Static Drain to Source On Resistance	$V_{GS} = 10\ \text{V}$, $I_D = 10\ \text{A}$	-	0.15	0.19	Ω
g_{FS}	Forward Transconductance	$V_{DS} = 40\ \text{V}$, $I_D = 10\ \text{A}$	-	17	-	S

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = 25\ \text{V}$, $V_{GS} = 0\ \text{V}$, $f = 1\ \text{MHz}$	-	2370	3080	pF
C_{oss}	Output Capacitance		-	1280	1665	pF
C_{rss}	Reverse Transfer Capacitance		-	95	-	pF
C_{oss}	Output Capacitance	$V_{DS} = 480\ \text{V}$, $V_{GS} = 0\ \text{V}$, $f = 1\ \text{MHz}$	-	65	85	pF
$C_{oss(eff.)}$	Effective Output Capacitance	$V_{DS} = 0\ \text{V}$ to $400\ \text{V}$, $V_{GS} = 0\ \text{V}$	-	165	-	pF
Q_g	Total Gate Charge at 10V	$V_{DS} = 480\ \text{V}$, $I_D = 20\ \text{A}$, $V_{GS} = 10\ \text{V}$ (Note 4)	-	75	98	nC
Q_{gs}	Gate to Source Gate Charge		-	13.5	18	nC
Q_{gd}	Gate to Drain "Miller" Charge		-	36	-	nC

Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 300\ \text{V}$, $I_D = 20\ \text{A}$, $V_{GS} = 10\ \text{V}$, $R_G = 25\ \Omega$ (Note 4)	-	62	135	ns
t_r	Turn-On Rise Time		-	140	290	ns
$t_{d(off)}$	Turn-Off Delay Time		-	230	470	ns
t_f	Turn-Off Fall Time		-	65	140	ns

Drain-Source Diode Characteristics

I _S	Maximum Continuous Drain to Source Diode Forward Current	-	-	20	A	
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current	-	-	60	A	
V _{SD}	Drain to Source Diode Forward Voltage	V _{GS} = 0 V, I _{SD} = 20 A	-	-	1.4	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0 V, I _{SD} = 20 A,	-	530	-	ns
Q _{rr}	Reverse Recovery Charge	dI _F /dt = 100 A/μs	-	10.5	-	μC

Notes:

- 1: Repetitive rating; pulse-width limited by maximum junction temperature.
- 2: $I_{AS} = 10\ \text{A}$, $V_{DD} = 50\ \text{V}$, $R_G = 25\ \Omega$, starting $T_J = 25^\circ\text{C}$.
- 3: $I_{SD} \leq 20\ \text{A}$, $di/dt \leq 200\ \text{A}/\mu\text{s}$, $V_{DD} \leq BV_{DSS}$, starting $T_J = 25^\circ\text{C}$.
- 4: Essentially independent of operating temperature typical characteristics.

Typical Performance Characteristics

Figure 1. On-Region Characteristics

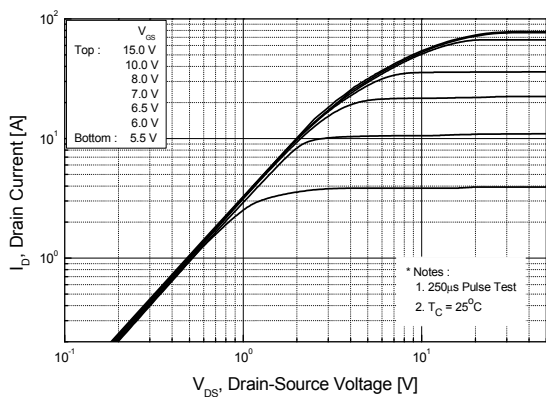


Figure 2. Transfer Characteristics

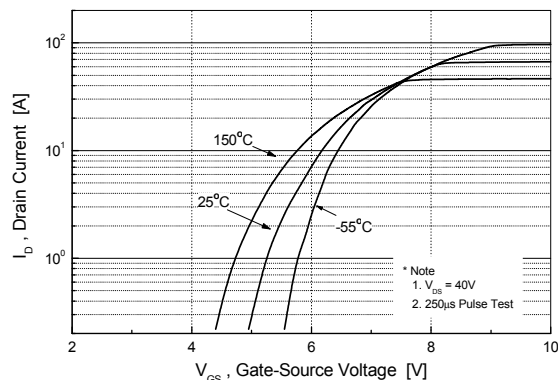


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

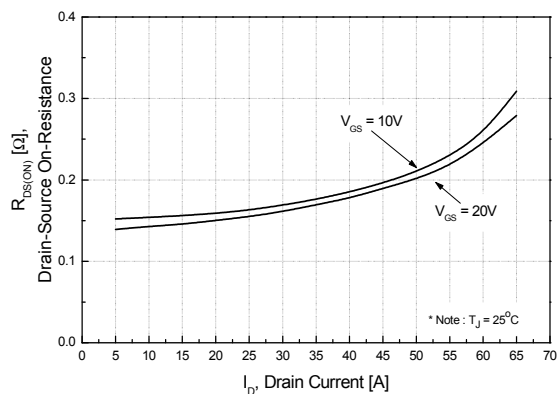


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

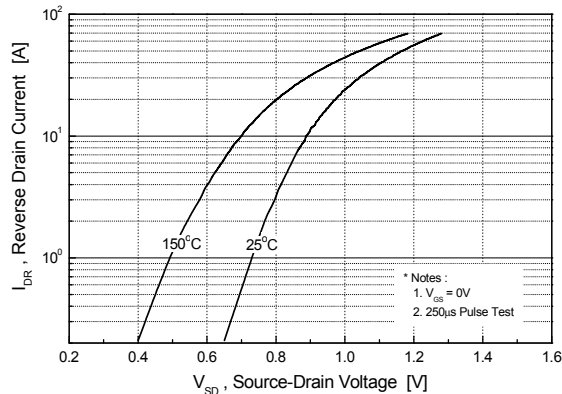


Figure 5. Capacitance Characteristics

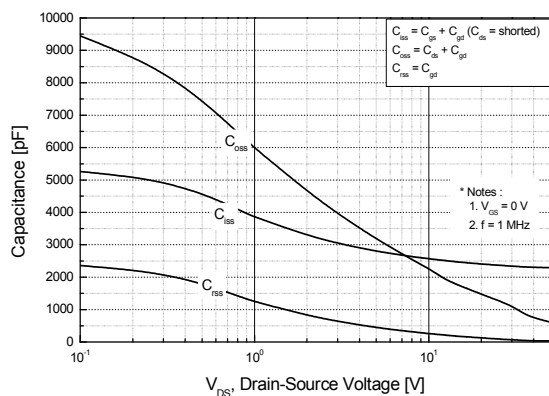
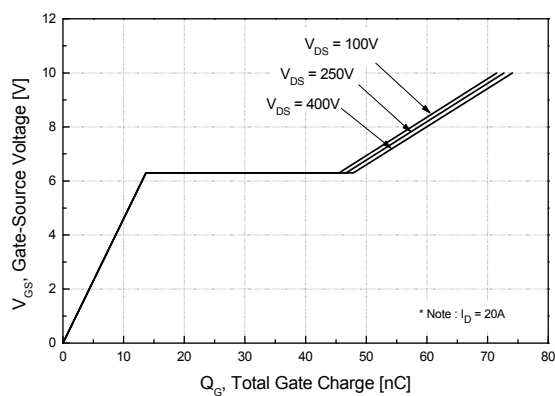


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

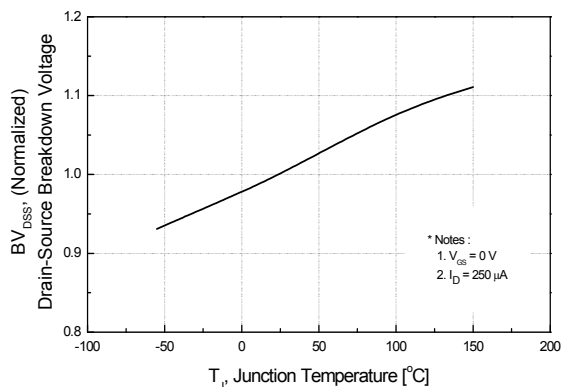


Figure 8. On-Resistance Variation vs. Temperature

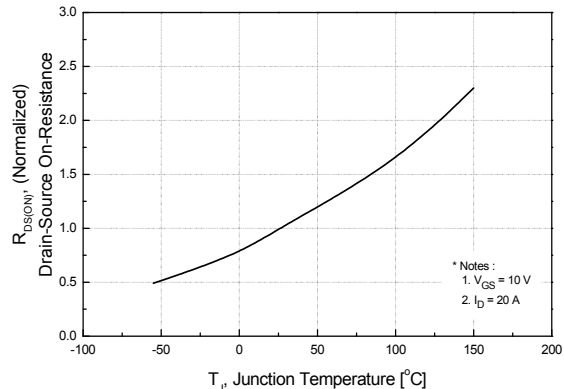


Figure 9. Maximum Safe Operating Area

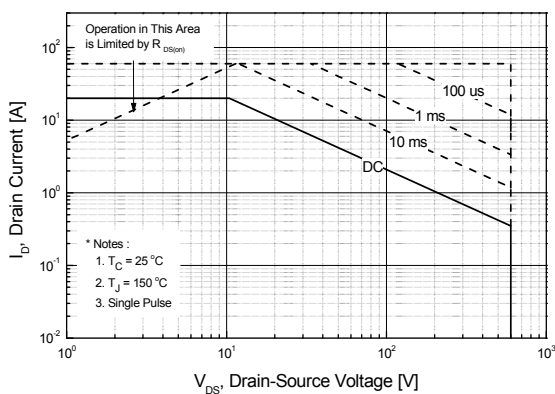


Figure 10. Maximum Drain Current vs. Case Temperature

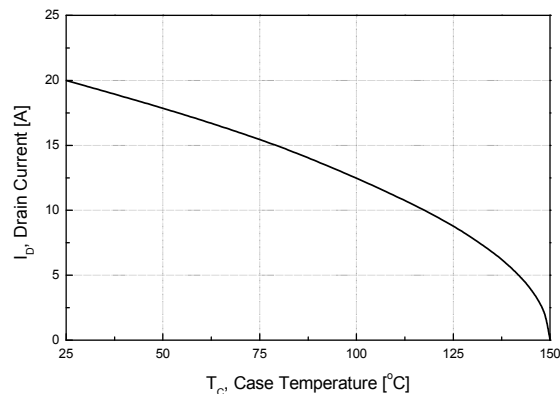
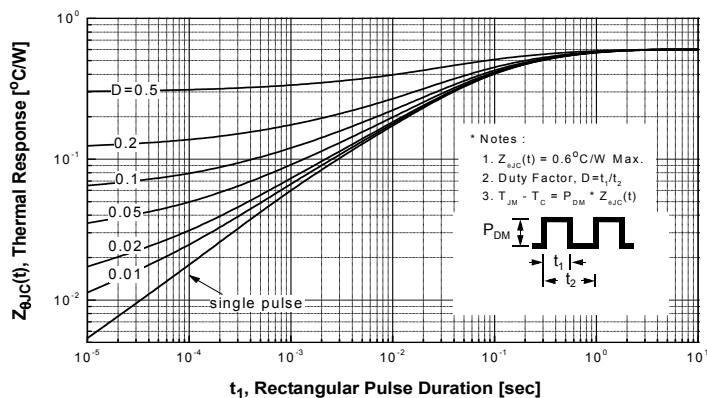


Figure 11. Transient Thermal Response Curve



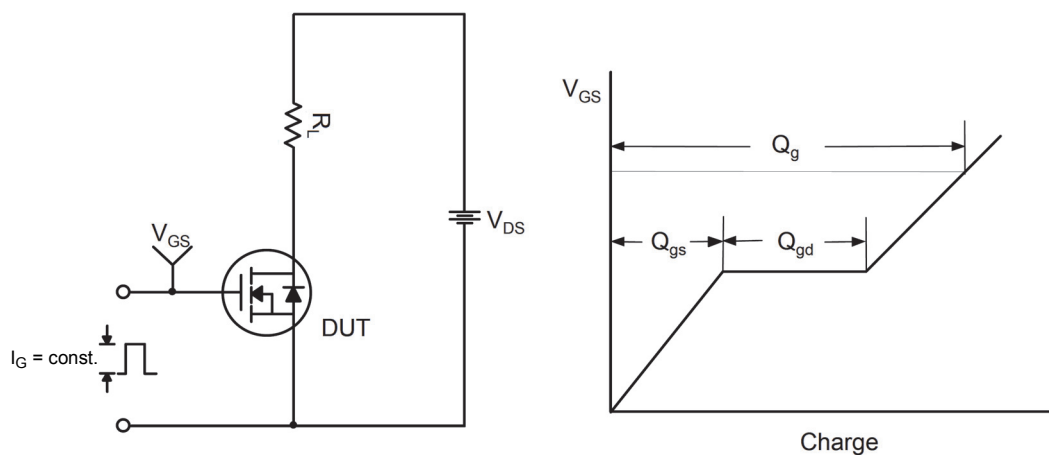


Figure 12. Gate Charge Test Circuit & Waveform

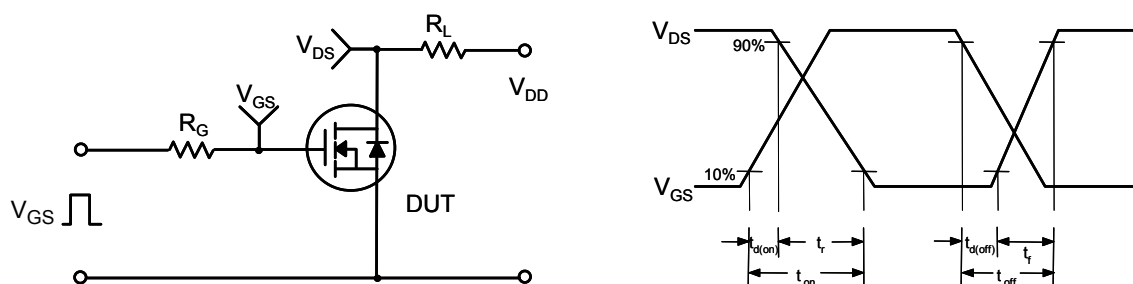


Figure 13. Resistive Switching Test Circuit & Waveforms

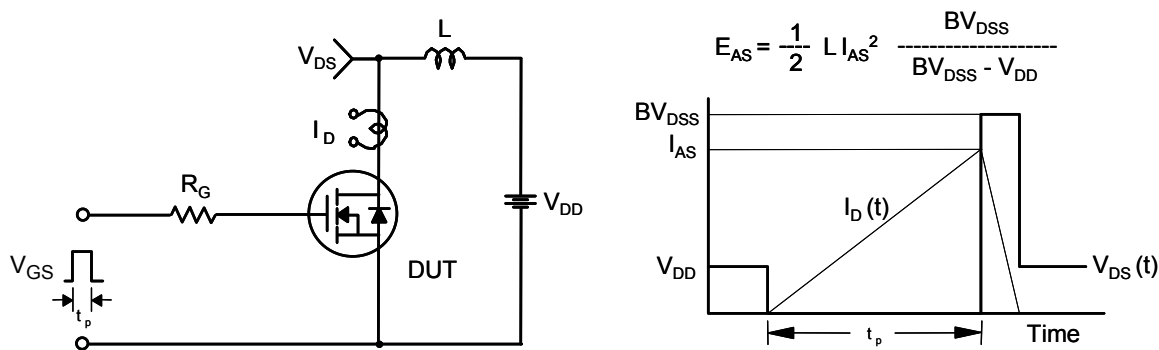


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

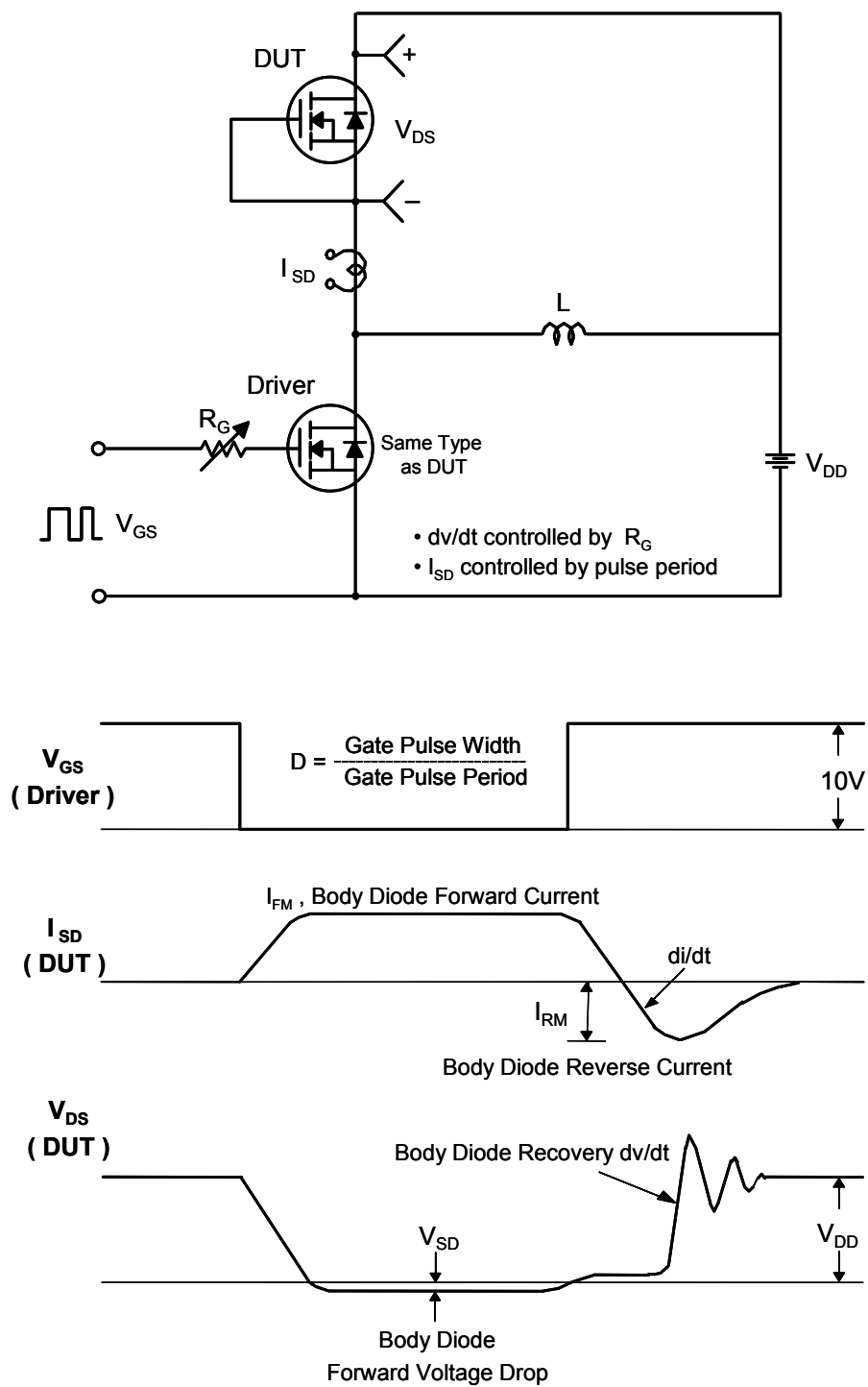


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

ON Semiconductor and  are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hold ON Semiconductor and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that ON Semiconductor was negligent regarding the design or manufacture of the part. ON Semiconductor is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor
19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA
Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada
Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada
Email: orderlit@onsemi.com

N. American Technical Support: 800-282-9855 Toll Free
USA/Canada

Europe, Middle East and Africa Technical Support:
Phone: 421 33 790 2910

Japan Customer Focus Center
Phone: 81-3-5817-1050

ON Semiconductor Website: www.onsemi.com

Order Literature: <http://www.onsemi.com/orderlit>

For additional information, please contact your local
Sales Representative